PBSS5112PAP

120 V, 1 A PNP/PNP low VCEsat (BISS) transistor 30 November 2012 Prod

Product data sheet

1. Product profile

1.1 General description

PNP/PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package. NPN/PNP complement: PBSS4112PANP. NPN/NPN complement: PBSS4112PAN.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- · Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

1.3 Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transist	Per transistor							
V_{CEO}	collector-emitter voltage	open base		-	-	-120	V	
I _C	collector current			-	-	-1	Α	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-1.5	Α	
V_{EBO}	emitter-base voltage	open collector		-	-	-7	V	
Per transist	Per transistor							
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C		-	-	440	mΩ	



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		P.
3	C2	collector TR2	7 8	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2		E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020-6 (SOT1118)	sym138
7	C1	collector TR1	DI 112020-0 (0011110)	
8	C2	collector TR2		

Ordering information 3.

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
PBSS5112PAP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118

Marking 4.

Marking codes Table 4.

Type number	Marking code
PBSS5112PAP	2S

Limiting values 5.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit		
Per transis	Per transistor							
V_{CBO}	collector-base voltage	open emitter		-	-120	V		
V_{CEO}	collector-emitter voltage	open base		-	-120	V		
V _{EBO}	emitter-base voltage	open collector		-	-7	V		
I _C	collector current			-	-1	Α		
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-1.5	Α		
I _B	base current			-	-0.3	Α		
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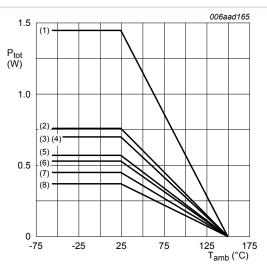
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Symbol	Parameter	Conditions	l l	Min	Max	Unit
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
			[5]	-	450	mW
			[6]	-	760	mW
			[7]	-	700	mW
		[8]	-	1450	mW	
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
		[2]	-	780	mW	
			[3]	-	730	mW
			[4]	-	960	mW
			[5]	-	620	mW
			[6]	-	1040	mW
			[7]	-	960	mW
			[8]	-	2000	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- 2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

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- (1) 4-layer PCB 70 μm, mounting pad for collector 1 cm²
- (2) FR4 PCB 70 µm, mounting pad for collector 1 cm²
- (3) 4-layer PCB 70 µm, standard footprint
- (4) 4-layer PCB 35 μm, mounting pad for collector 1 cm²
- (5) FR4 PCB 35 μm, mounting pad for collector 1 cm²
- (6) 4-layer PCB 35 µm, standard footprint
- (7) FR4 PCB 70 µm, standard footprint
- (8) FR4 PCB 35 µm, standard footprint

Fig. 1. Per transistor: power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transist	Per transistor								
R _{th(j-a)}		[1]	-	-	338	K/W			
	from junction to ambient	1	[2]	-	-	219	K/W		
ambient	1	[3]	-	-	236	K/W			
		[5] [6]	[4]	-	-	179	K/W		
			[5]	-	-	278	K/W		
			[6]	-	-	164	K/W		
			[7]	-	-	179	K/W		
			[8]	-	-	86	K/W		
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W		

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							_
R _{th(j-a)}	thermal resistance in free air	[1]	-	-	245	K/W	
	from junction to		[2]	-	-	160	K/W
	ambient		[3]	-	-	171	K/W
		[4]	-	-	130	K/W	
			[5]	-	-	202	K/W
		[6]	-	-	120	K/W	
		[7]	-	-	130	K/W	
			[8]	-	-	63	K/W

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

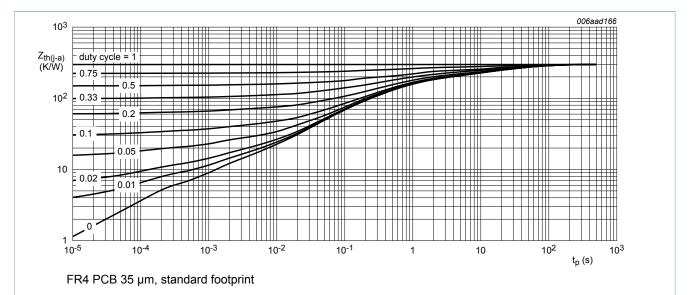
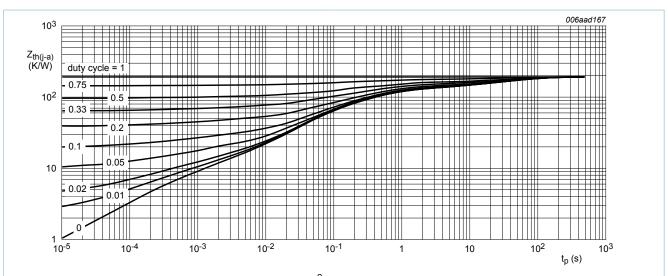


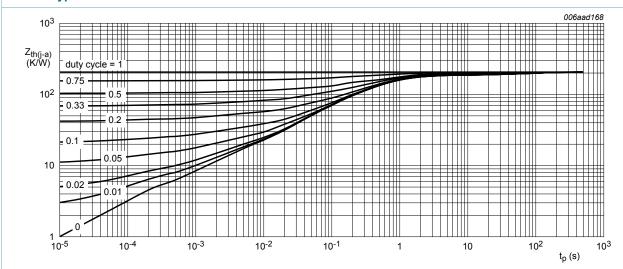
Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB 35 µm, mounting pad for collector 1 cm²

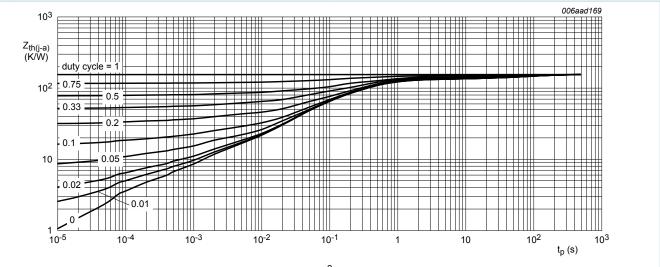
Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 35 µm, standard footprint

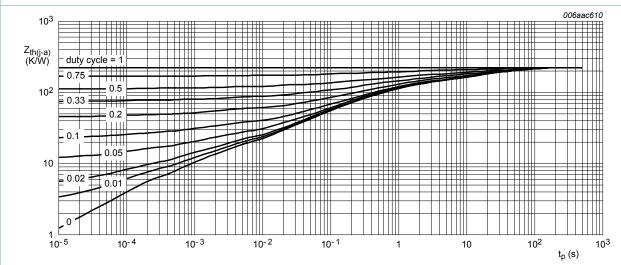
Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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4-layer PCB 35 μm, mounting pad for collector 1 cm²

Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB 70 µm, standard footprint

Fig. 6. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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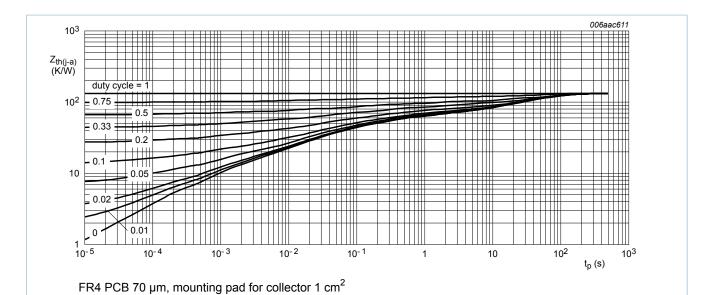
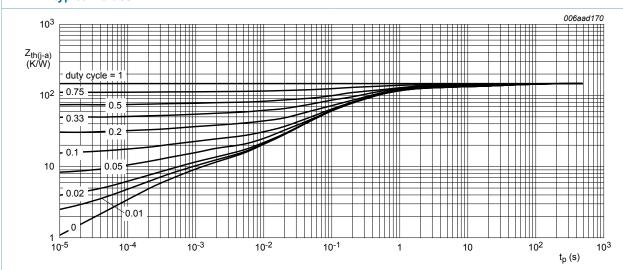


Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



4-layer PCB 70 μm, standard footprint

Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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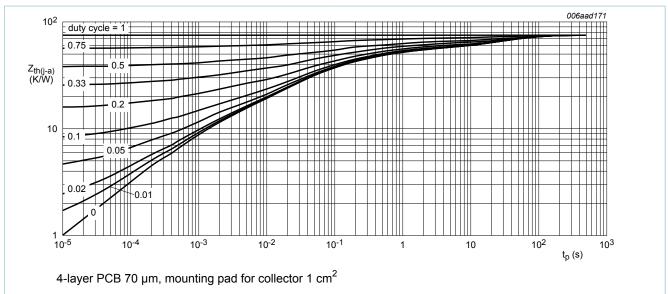


Fig. 9. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

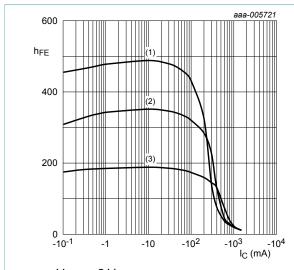
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
I _{CBO}	collector-base cut-off	V _{CB} = -96 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -96 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE} DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	190	305	-		
		V_{CE} = -2 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	50	85	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	15	25	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-150	-220	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-335	-480	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	440	mΩ
V_{BEsat}	base-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-	-1	V

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Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
		I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-	-0.9	V
t _d	delay time	V _{CC} = -10 V; I _C = -500 mA;	-	-	15	-	ns
t _r	rise time	$I_{Bon} = -25 \text{ mA}; I_{Boff} = 25 \text{ mA};$	-	-	245	-	ns
t _{on}	turn-on time	T _{amb} = 25 °C	-	-	260	-	ns
ts	storage time		-	-	290	-	ns
t _f	fall time		-	-	270	-	ns
t _{off}	turn-off time		-	-	560	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	Ę	50	100	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	9.5	13	pF



 $V_{CE} = -2 V$

(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. DC current gain as a function of collector current; typical values

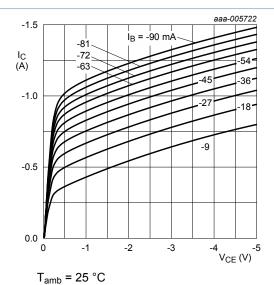
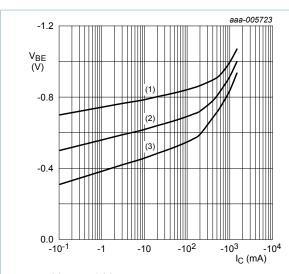


Fig. 11. Collector current as a function of collectoremitter voltage; typical values

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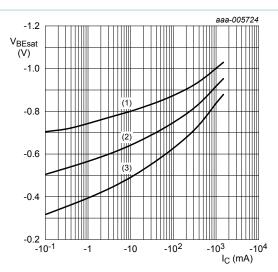
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. Base-emitter voltage as a function of collector current; typical values



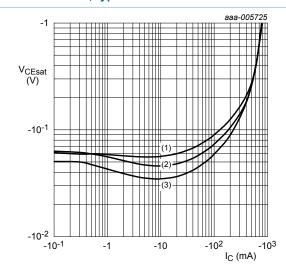
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 13. Base-emitter saturation voltage as a function of collector current; typical values



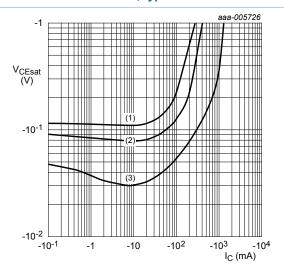
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values



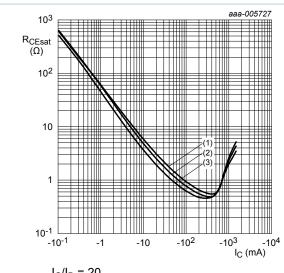
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation voltage as a function of collector current; typical values

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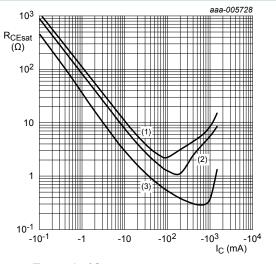
$$I_C/I_B = 20$$

(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 16. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 100$$

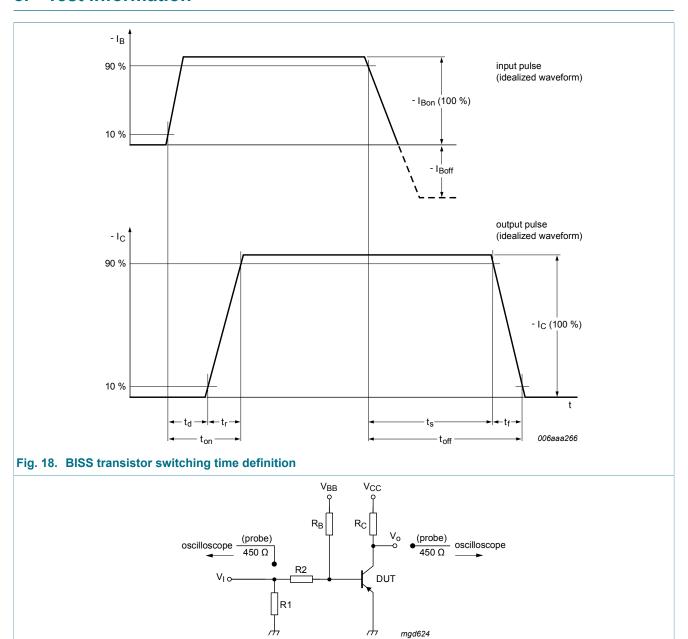
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 17. Collector-emitter saturation resistance as a function of collector current; typical values

120 V, 1 A PNP/PNP low VCEsat (BISS) transistor

8. Test information



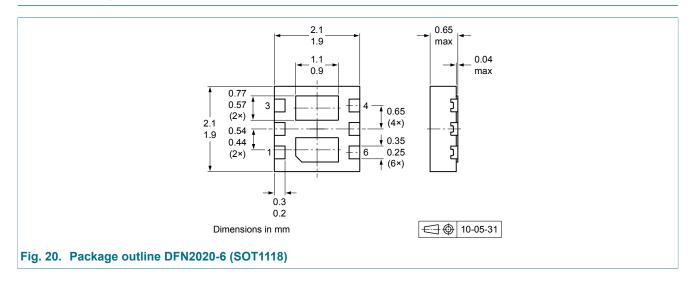
8.1 Quality information

Fig. 19. Test circuit for switching times

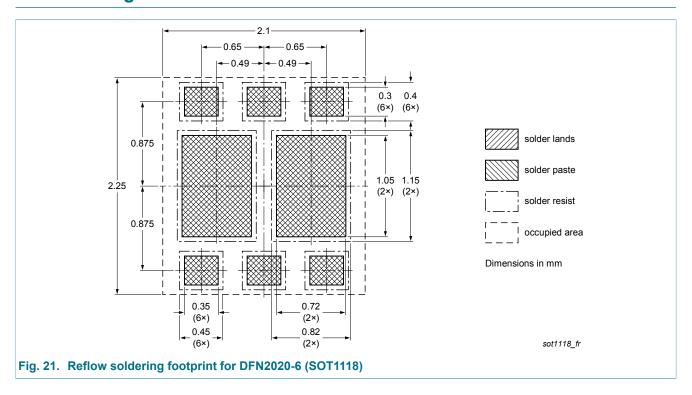
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Soldering



11. Revision history

Table 8. Revision history

The first the fi							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS5112PAP v.1	20121130	Product data sheet	-	-			

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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